

1.2V Drive Nch MOSFET

RUU002N05

Structure

Silicon N-channel MOSFET

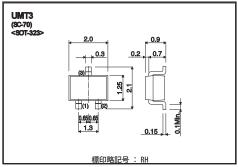
Features

- 1) High speed switing.
- 2) Small package(UMT3).
 3) Ultra low voltage drive(1.2V drive).

Application

Switching

Dimensions (Unit : mm)



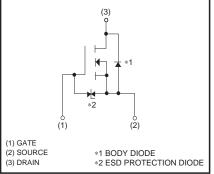
Packaging specifications

	Package	Taping
Туре	Code	T106
	Basic ordering unit (pieces)	3000
RUU002N0	05	0



Unit V V mΑ mΑ mΑ mΑ mW °C

°C



Param	neter	Symbol	Limits
Drain-source voltage		V _{DSS}	50
Gate-source voltage		V _{GSS}	±8
Drain current	Continuous	I _D	±200
	Pulsed	<mark>ا</mark> 1 ا	±800
Source current	Continuous		150

Drain current		D	
	Pulsed	<mark>ا</mark> 1 ا	±800
Source current	Continuous	I _S	150
(Body Diode)	Pulsed	ا _{sP} 1	800
Power dissipation		P _D *2	200
Channel temperature		Tch	150

*1 Pw≤10µs, Duty cycle≤1%

Range of storage temperature

*2 Each terminal mounted on a recommended land.

•Absolute maximum ratings (Ta = 25°C)

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	625	°C / W

Tsta

* Each terminal mounted on a recommended land

-55 to +150

•Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	50	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =50V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	-	1.0	V	V _{DS} =10V, I _D =1mA
		-	1.6	2.2		I _D =200mA, V _{GS} =4.5\
Ctatia drain aguras en stata		-	1.7	2.4		I _D =200mA, V _{GS} =2.5\
Static drain-source on-state resistance	R _{DS (on)}	-	1.9	2.7	Ω	I _D =100mA, V _{GS} =1.8\
resistance		-	2.0	4.0		I _D =40mA, V _{GS} =1.5V
		-	2.4	7.2		I _D =20mA, V _{GS} =1.2V
Forward transfer admittance	۱ Y _{fs} ľ	0.4	-	-	S	I _D =200mA, V _{DS} =10V
Input capacitance	C _{iss}	-	25	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	6	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	3	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	4	-	ns	I _D =100mA, V _{DD} ≒ 30∖
Rise time	t _r *	-	6	-	ns	V _{GS} =4.5V
Turn-off delay time	t _{d(off)} *	-	15	-	ns	R _L =300Ω
Fall time	t _f *	-	55	-	ns	R _G =10Ω

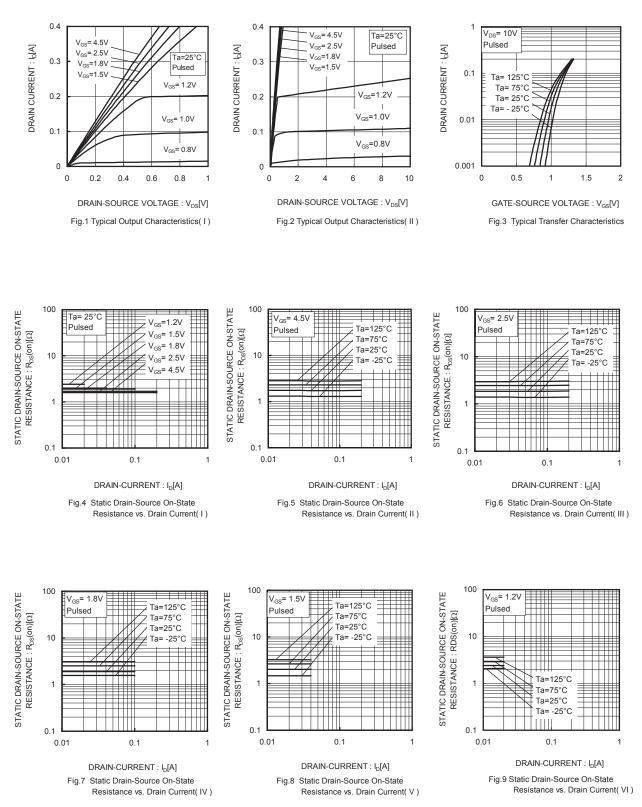
*Pulsed

•Body diode characteristics (Source-Drain) (Ta = 25°C)

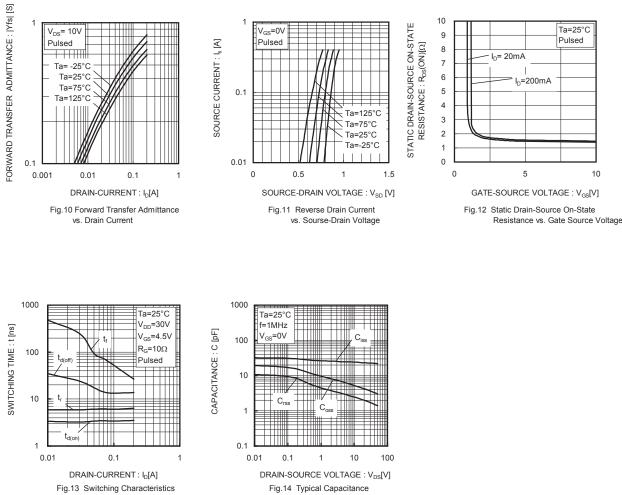
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V_{SD}^{*}	-	-	1.2	V	I _s =200mA, V _{GS} =0V

*Pulsed

•Electrical characteristic curves



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vs. Drain-Source Voltage

Measurement circuits

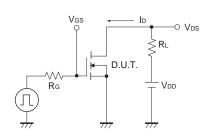


Fig.1-1 Switching time measurement circuit

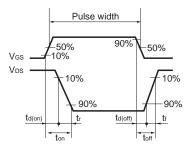


Fig.1-2 Switching waveforms

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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